



3.3V CMOS 20-BIT BUFFER

IDT74FCT163827A/B/C

FEATURES:

- 0.5 MICRON CMOS Technology
- Typical $t_{sk(o)}$ (Output Skew) < 250ps
- ESD > 2000V per MIL-STD-883, Method 3015;
> 200V using machine model (C = 200pF, R = 0)
- $V_{cc} = 3.3V \pm 0.3V$, Normal Range or $V_{cc} = 2.7V$ to 3.6V, Extended Range
- CMOS power levels (0.4μW typ. static)
- Rail-to-Rail output swing for increased noise margin
- Low Ground Bounce (0.3V typ.)
- Inputs (except I/O) can be driven by 3.3V or 5V components
- Available in SSOP, TSSOP and TVSOP Packages

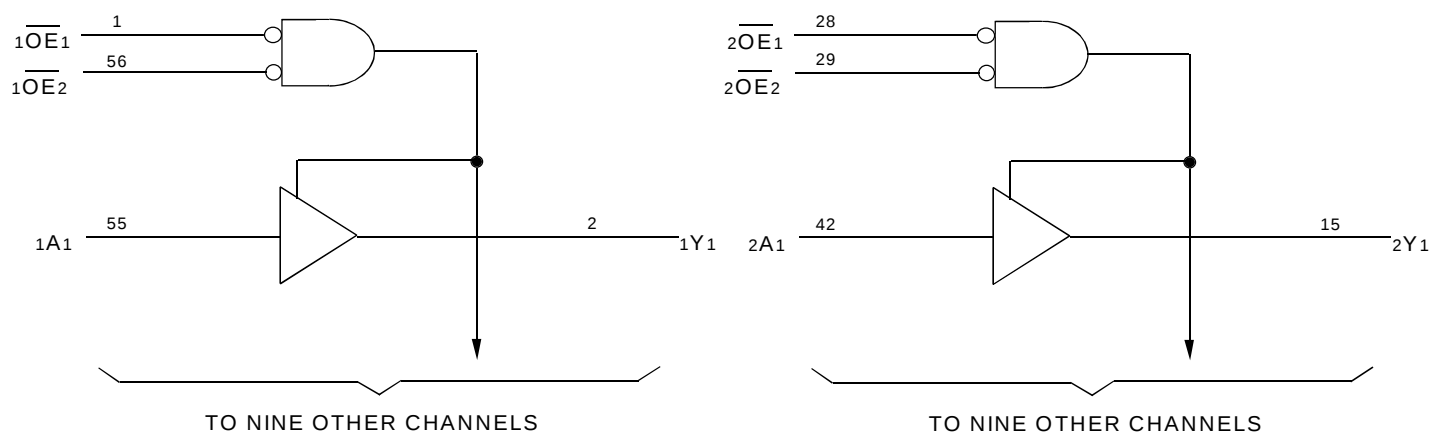
DESCRIPTION:

The FCT163827A/B/C 20-bit buffers are built using advanced dual metal CMOS technology. These 20-bit bus drivers provide high-performance bus interface buffering for wide data/address paths or busses carrying parity. Two pairs of NAND-ed output enable controls offer maximum control flexibility and are organized to operate the device as two 10-bit buffers or one 20-bit buffer. Flow-through organization of signal pins simplifies layout. All inputs are designed with hysteresis for improved noise margin.

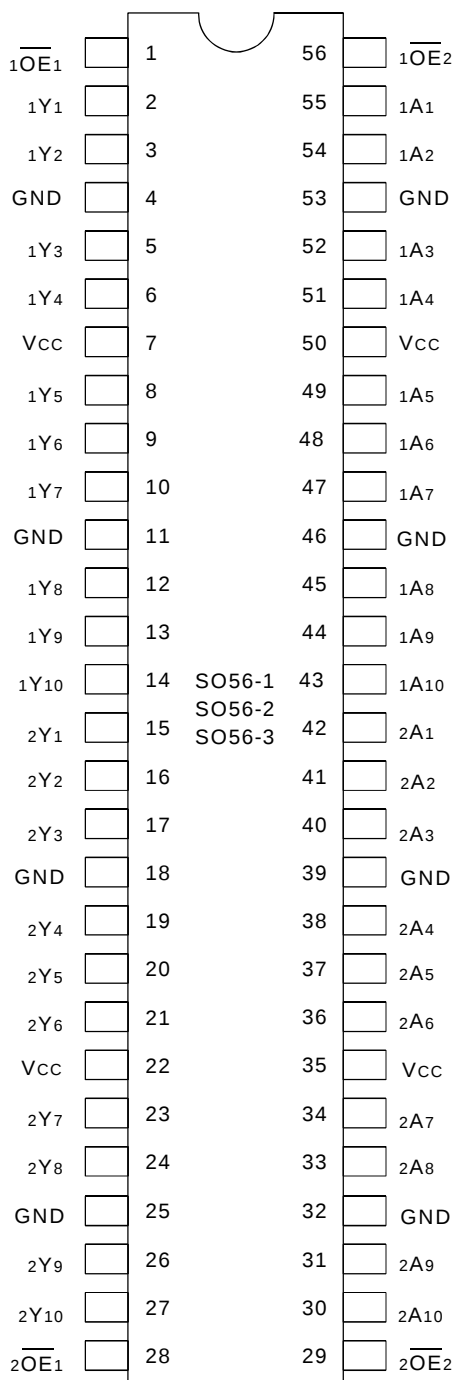
The FCT163827A/B/C have series current limiting resistors. This offers low ground bounce, minimal undershoot, and controlled output fall times, reducing the need for external series terminating resistors.

The inputs of the FCT163827A/B/C can be driven from either 3.3V or 5V devices. This feature allows the use of these devices as translators in a mixed 3.3V/5V supply system.

FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATION



SSOP/ TSSOP/ TVSOP
TOP VIEW

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Description	Max	Unit
V _{TERM} ⁽²⁾	Terminal Voltage with Respect to GND	−0.5 to +4.6	V
V _{TERM} ⁽³⁾	Terminal Voltage with Respect to GND	−0.5 to +7	V
V _{TERM} ⁽⁴⁾	Terminal Voltage with Respect to GND	−0.5 to V _{CC} +0.5	V
T _{STG}	Storage Temperature	−65 to +150	°C
I _{OUT}	DC Output Current	−60 to +60	mA

3v16-link

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- V_{CC} terminals.
- Input terminals.
- Outputs and I/O terminals.

CAPACITANCE (T_A = +25°C, f = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Typ.	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	3.5	6	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0V	3.5	8	pF

3v16-link

NOTE:

- This parameter is measured at characterization but not tested.

PIN DESCRIPTION

Pin Names	Description
x $\overline{OE}$ x	Output Enable Inputs (Active LOW)
xAx	Data Inputs
xYx	3-State Outputs

FUNCTION TABLE (1)

Inputs			Outputs
x $\overline{OE}$ 1	x $\overline{OE}$ 2	xAx	xYx
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

NOTE:

- H = HIGH Voltage Level
L = LOW Voltage Level
X = Don't Care
Z = High-Impedance

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

Industrial: $T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_{CC} = 2.7\text{V}$ to 3.6V

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Typ. ⁽²⁾	Max.	Unit
V_{IH}	Input HIGH Level (Input pins)	Guaranteed Logic HIGH Level		2	—	5.5	V
	Input HIGH Level (I/O pins)			2	—	$V_{CC}+0.5$	
V_{IL}	Input LOW Level (Input and I/O pins)	Guaranteed Logic LOW Level		-0.5	—	0.8	V
I_{IH}	Input HIGH Current (Input pins)	$V_{CC} = \text{Max.}$	$V_I = 5.5\text{V}$	—	—	± 1	μA
	Input HIGH Current (I/O pins)		$V_I = V_{CC}$	—	—	± 1	
I_{IL}	Input LOW Current (Input pins)		$V_I = \text{GND}$	—	—	± 1	
	Input LOW Current (I/O pins)		$V_I = \text{GND}$	—	—	± 1	
I_{OZH}	High Impedance Output Current	$V_{CC} = \text{Max.}$	$V_O = V_{CC}$	—	—	± 1	μA
I_{OZL}	(3-State Output pins)		$V_O = \text{GND}$	—	—	± 1	
V_{IK}	Clamp Diode Voltage	$V_{CC} = \text{Min.}, I_{IN} = -18\text{mA}$		—	-0.7	-1.2	V
I_{ODH}	Output HIGH Current	$V_{CC} = 3.3\text{V}, V_{IN} = V_{IH} \text{ or } V_{IL}, V_O = 1.5\text{V}^{(3)}$		-36	-60	-110	mA
I_{ODL}	Output LOW Current	$V_{CC} = 3.3\text{V}, V_{IN} = V_{IH} \text{ or } V_{IL}, V_O = 1.5\text{V}^{(3)}$		50	90	200	mA
V_{OH}	Output HIGH Voltage	$V_{CC} = \text{Min.}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -0.1\text{mA}$	$V_{CC}-0.2$	—	—	V
			$I_{OH} = -3\text{mA}$	2.4	3	—	
		$V_{CC} = 3\text{V}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -8\text{mA}$	2.4 ⁽⁵⁾	3	—	
V_{OL}	Output LOW Voltage	$V_{CC} = \text{Min.}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 0.1\text{mA}$	—	—	0.2	V
			$I_{OL} = 16\text{mA}$	—	0.2	0.4	
			$I_{OL} = 24\text{mA}$	—	0.3	0.55	
		$V_{CC} = 3\text{V}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 24\text{mA}$		0.3	0.5	
I_{OS}	Short Circuit Current ⁽⁴⁾	$V_{CC} = \text{Max.}, V_O = \text{GND}^{(3)}$		-60	-135	-240	mA
V_H	Input Hysteresis	—		—	150	—	mV
I_{CCL} I_{CCH} I_{CCZ}	Quiescent Power Supply Current	$V_{CC} = \text{Max.}$ $V_{IN} = \text{GND or } V_{CC}$		—	0.1	10	μA

3v16-link

NOTES:

- For conditions shown as Max. or Min., use appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical values are at $V_{CC} = 3.3\text{V}$, $+25^{\circ}\text{C}$ ambient.
- Not more than one output should be tested at one time. Duration of the test should not exceed one second.
- This parameter is guaranteed but not tested.
- $V_{OH} = V_{CC} - 0.6\text{V}$ at rated current.

POWER SUPPLY CHARACTERISTICS

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Typ. ⁽²⁾	Max.	Unit
ΔI_{CC}	Quiescent Power Supply Current TTL Inputs HIGH	$V_{CC} = \text{Max.}$	$V_{IN} = V_{CC} - 0.6V^{(3)}$	—	2	30	μA
I_{CCD}	Dynamic Power Supply Current ⁽⁴⁾	$V_{CC} = \text{Max.}$ Outputs Open $\overline{xOE}_1 = \overline{xOE}_2 = \text{GND}$ One Input Toggling 50% Duty Cycle	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	50	75	$\mu A / \text{MHz}$
I_C	Total Power Supply Current ⁽⁶⁾	$V_{CC} = \text{Max.}$ Outputs Open $f_i = 10\text{MHz}$ 50% Duty Cycle $\overline{xOE}_1 = \overline{xOE}_2 = \text{GND}$ One Bit Toggling	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	0.5	0.7	mA
			$V_{IN} = V_{CC} - 0.6V$ $V_{IN} = \text{GND}$	—	0.5	0.8	
		$V_{CC} = \text{Max.}$ Outputs Open $f_i = 2.5\text{MHz}$ 50% Duty Cycle $\overline{xOE}_1 = \overline{xOE}_2 = \text{GND}$ Twenty Bits Toggling	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	2.5	3.7 ⁽⁵⁾	
			$V_{IN} = V_{CC} - 0.6V$ $V_{IN} = \text{GND}$	—	2.5	4.1 ⁽⁵⁾	

NOTES:

- For conditions shown as max. or min., use appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical values are at $V_{CC} = 3.3V$, $+25^\circ\text{C}$ ambient.
- Per TTL driven input; all other inputs at V_{CC} or GND .
- This parameter is not directly testable, but is derived for use in Total Power Supply Calculations.
- Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.
- $I_C = I_{\text{QUIESCENT}} + I_{\text{INPUTS}} + I_{\text{DYNAMIC}}$
 $I_C = I_{CC} + \Delta I_{CC} \text{ DHNT} + I_{CCD} (f_{CP} N_{CP} / 2 + f_i N_i)$
 $I_{CC} = \text{Quiescent Current (} I_{CCL}, I_{CCH} \text{ and } I_{CCZ} \text{)}$
 $\Delta I_{CC} = \text{Power Supply Current for a TTL High Input}$
 $\text{DH} = \text{Duty Cycle for TTL Inputs High}$
 $\text{NT} = \text{Number of TTL Inputs at DH}$
 $I_{CCD} = \text{Dynamic Current Caused by an Input Transition Pair (HLH or LHL)}$
 $f_{CP} = \text{Clock Frequency for Register Devices (Zero for Non-Register Devices)}$
 $N_{CP} = \text{Number of Clock Inputs at } f_{CP}$
 $f_i = \text{Input Frequency}$
 $N_i = \text{Number of Inputs at } f_i$

SWITCHING CHARACTERISTICS OVER OPERATING RANGE (4)

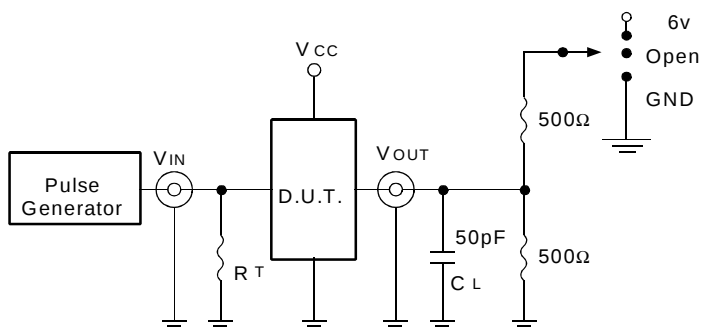
Symbol	Parameter	Conditions ⁽¹⁾	FCT163827A		FCT163827B		FCT163827C		Unit
			Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	
tPLH tPHL	Propagation Delay xAx to xYx	CL = 50pF RL = 500Ω	1.5	8	1.5	5	1.5	4.4	ns
		CL = 300pF ⁽⁴⁾ RL = 500Ω	1.5	15	1.5	13	1.5	10	
tpZH tpZL	Output Enable Time xOE $\bar{x}$ to xYx	CL = 50pF RL = 500Ω	1.5	12	1.5	8	1.5	7	ns
		CL = 300pF ⁽⁴⁾ RL = 500Ω	1.5	23	1.5	15	1.5	14	
tpHZ tpLZ	Output Disable Time xOE $\bar{x}$ to xYx	CL = 5pF ⁽⁴⁾ RL = 500Ω	1.5	9	1.5	6	1.5	5.7	ns
		CL = 50pF RL = 500Ω	1.5	10	1.5	7	1.5	6	
tsk(0)	Output Skew ⁽³⁾		—	0.5	—	0.5	—	0.5	ns

NOTES:

1. See test circuit and waveforms.
2. Minimum limits are guaranteed but not tested on Propagation Delays.
3. Skew between any two outputs, of the same package, switching in the same direction. This parameter is guaranteed by design.
4. Propagation Delays and Enable/Disable times are with Vcc = 3.3V ±0.3V, Normal Range. For Vcc = 2.7V to 3.6V, Extended Range, all Propagation Delays and Enable/Disable times should be degraded by 20%.

TEST CIRCUITS AND WAVEFORMS

TEST CIRCUITS FOR ALL OUTPUTS



SWITCH POSITION

Test	Switch
Open Drain Disable Low Enable Low	6V
Disable High Enable High	GND
All Other Tests	Open

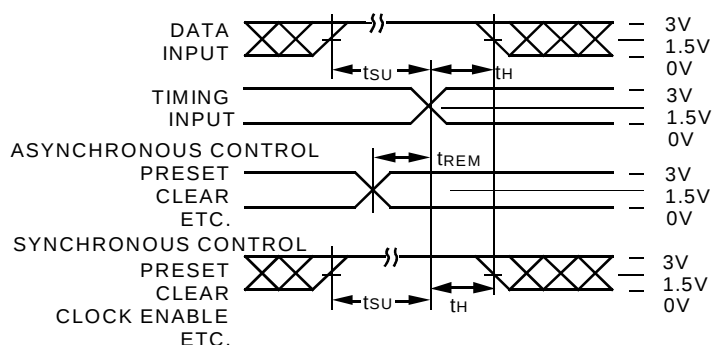
3v16-link

DEFINITIONS:

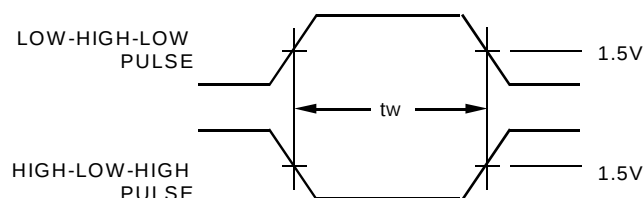
C_L = Load capacitance: includes jig and probe capacitance.

R_T = Termination resistance: should be equal to Z_{OUT} of the Pulse Generator.

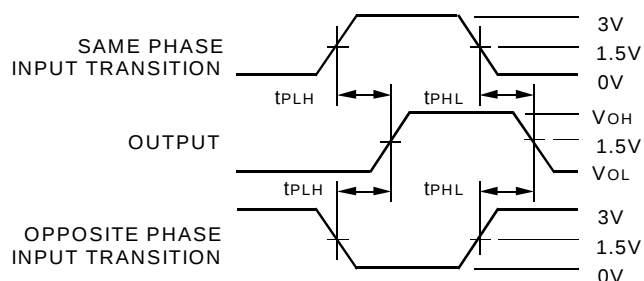
SET-UP, HOLD, AND RELEASE TIMES



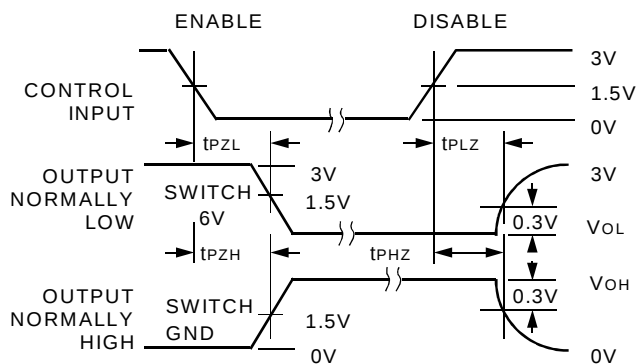
PULSE WIDTH



PROPAGATION DELAY



ENABLE AND DISABLE TIMES



NOTES:

- Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.
- Pulse Generator for All Pulses: Rate $\leq 1.0\text{MHz}$; $t_F \leq 2.5\text{ns}$; $t_R \leq 2.5\text{ns}$.
- If V_{CC} is below 3V, input voltage swings should be adjusted not to exceed V_{CC} .

ORDERING INFORMATION

IDT	XX	FCT	XXX	XXXX	X		
Temp. Range	Family		Device Type	Package			
					PV	Shrink Small Outline Package (SO56-1)	
					PA	Thin Shrink Small Outline Package (SO56-2)	
					PF	Thin Very Small Outline Package (SO56-3)	
					827A	Non-Inverting 20-Bit Buffer	
					827B		
					827C		
					163	Double-Density 3.3Volt	
					74	- 40°C to +85°C	



CORPORATE HEADQUARTERS
 2975 Stender Way
 Santa Clara, CA 95054

for SALES:
 800-345-7015 or 408-727-6116
 fax: 408-492-8674
www.idt.com*

**To search for sales office near you, please click the sales button found on our home page or dial the 800# above and press 2.*
 The IDT logo is a registered trademark of Integrated Device Technology, Inc.